



[10191/1993]

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant : Richard SPITZ et al.

Serial No. : 09/914,404

Filed : December 13, 2001

For : **METHOD FOR PRODUCING HEAVILY-DOPED SEMICONDUCTOR COMPONENTS**

Group Art Unit : 2823

Examiner : Michelle Estrada

Commissioner for Patents  
Washington, D.C. 20231  
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**AMENDMENT AFTER FINAL OFFICE ACTION**

SIR:

In response to the Final Office Action mailed on November 20, 2002, please reconsider the above-identified application based on the following:

**IN THE CLAIMS:**

Please amend without prejudice the claims as follows:

13. (Twice Amended) A method for producing a semiconductor component in which at least one doped region is introduced into a semiconductor wafer, comprising the steps of:

applying a solid glass layer provided with a dopant on at least one of two sides of the semiconductor wafer;

heating the semiconductor wafer to a high temperature while the glass layer is applied so that the dopant from the solid glass layer penetrates into the semiconductor wafer to produce the at least one doped region;

removing the solid glass layer; and

providing the dopant at a dosage of at least  $10^{17}/\text{cm}^2$  in the at least one doped region.